# NSN 5962-01-254-9110

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# **Overall Height:**

0.425 inches

# **Body Length:**

1.290 inches

# Body Width:

Between 0.500 inches and 0.610 inches

#### **Body Height:**

Between 0.150 inches and 0.210 inches

# **Maximum Power Dissipation Rating:**

1.2 watts

# **Operating Tempurature Range:**

-55.0/+125.0 degrees celsius

#### Storage Tempurature Range:

-65.0/+150.0 degrees celsius

#### **Features Provided:**

High impedance and 3-state output and w/active pull-up and monolithic and burn in and schottky and programmable and bipolar

#### Inclosure Material:

Ceramic

# Inclosure Configuration:

Dual-in-line

# Output Logic Form:

Transistor-transistor logic

#### Input Circuit Pattern:

14 input

# **Case Outline Source And Designator:**

D-3 mil-m-38510

# **Terminal Surface Treatment:**

Solder

# Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

#### **Time Rating Per Chacteristic:**

100.00 nanoseconds propagation delay time, low to high level output and 100.00 nanoseconds propagation delay time, high to low level

output

#### Memory Device Type:

Rom

#### **Test Data Document:**

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

# **Terminal Type And Quantity:**

24 printed circuit

#### Shelf Life:

N/a

### Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0

